

Complementary 20 V (D-S) MOSFET

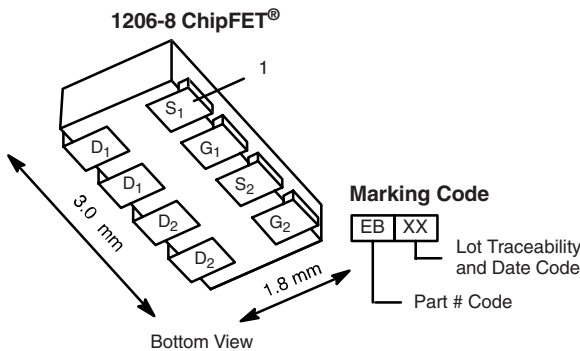
PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
N-Channel	20	0.075 at V _{GS} = 4.5 V	4.2	4
		0.134 at V _{GS} = 2.5 V	3.1	
P-Channel	- 20	0.155 at V _{GS} = - 4.5 V	- 2.9	3
		0.260 at V _{GS} = - 2.5 V	- 2.2	

FEATURES

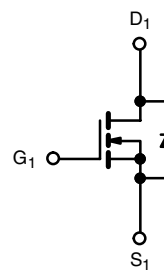
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC



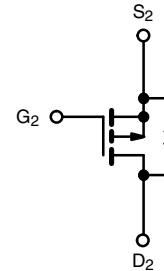
RoHS
COMPLIANT
HALOGEN
FREE
Available



Ordering Information: Si5513DC-T1-E3 (Lead (Pb)-free)
Si5513DC-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter		Symbol	N-Channel		P-Channel		Unit
			5 s	Steady State	5 s	Steady State	
Drain-Source Voltage		V _{DS}	20		- 20		V
Gate-Source Voltage		V _{GS}	± 12				
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	4.2	3.1	- 2.9	- 2.1	A
	T _A = 85 °C		3.0	2.2	- 2.1	- 1.5	
Pulsed Drain Current		I _{DM}	10		- 10		
Continuous Source Current (Diode Conduction) ^a		I _S	1.8	0.9	- 1.8	- 0.9	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.1	1.1	2.1	1.1	W
	T _A = 85 °C		1.1	0.6	1.1	0.6	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150				°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260				

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 s	R _{thJA}	50	60	°C/W
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	30	40	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. See reliability manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	0.6		1.5	V
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 0.6		- 1.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V	N-Ch P-Ch			± 100 ± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	N-Ch			1	μA
		V _{DS} = - 20 V, V _{GS} = 0 V	P-Ch			- 1	
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 70 °C	N-Ch			5	
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 70 °C	P-Ch			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	N-Ch	10			A
		V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	P-Ch	- 10			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 3.1 A	N-Ch		0.065	0.075	Ω
		V _{GS} = - 4.5 V, I _D = - 2.1 A	P-Ch		0.130	0.155	
		V _{GS} = 2.5 V, I _D = 2.3 A	N-Ch		0.115	0.134	
		V _{GS} = - 2.5 V, I _D = - 1.7 A	P-Ch		0.215	0.260	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 3.1 A	N-Ch		8		S
		V _{DS} = - 10 V, I _D = - 2.1 A	P-Ch		5		
Diode Forward Voltage ^a	V _{SD}	I _S = 0.9 A, V _{GS} = 0 V	N-Ch		0.8	1.2	V
		I _S = - 0.9 A, V _{GS} = 0 V	P-Ch		- 0.8	- 1.2	
Dynamic ^b							
Total Gate Charge	Q _g	N-Channel V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 3.1 A	N-Ch		4	6	nC
Gate-Source Charge	Q _{gs}		P-Ch		3	6	
Gate-Drain Charge	Q _{gd}	P-Channel V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 2.1 A	N-Ch P-Ch		0.6 0.9		
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 10 V, R _L = 10 Ω I _D ≅ 1 A, V _{GEN} = 4.5 V, R _g = 6 Ω	N-Ch P-Ch		12 13	18 20	ns
Rise Time	t _r		N-Ch P-Ch		35 35	55 55	
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 10 V, R _L = 10 Ω I _D ≅ - 1 A, V _{GEN} = - 4.5 V, R _g = 6 Ω	N-Ch P-Ch		19 25	30 40	
Fall Time	t _f		N-Ch P-Ch		9 25	15 40	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 0.9 A, dI/dt = 100 A/μs	N-Ch		40	80	
		I _F = - 0.9 A, dI/dt = 100 A/μs	P-Ch		40	80	

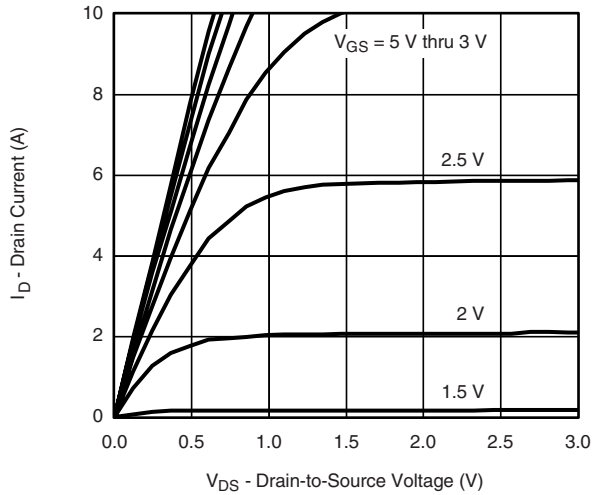
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

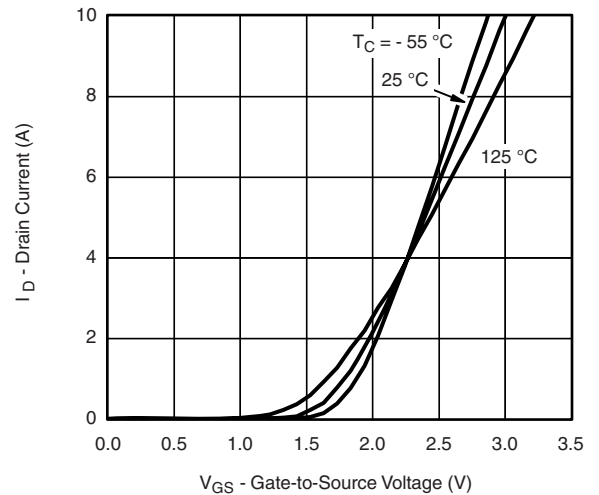
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

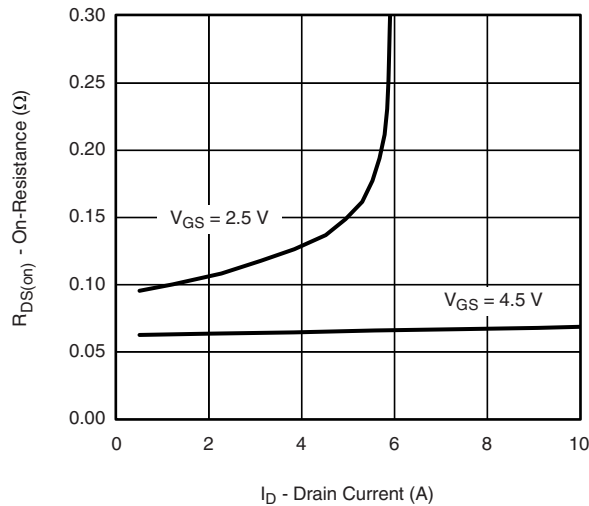
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



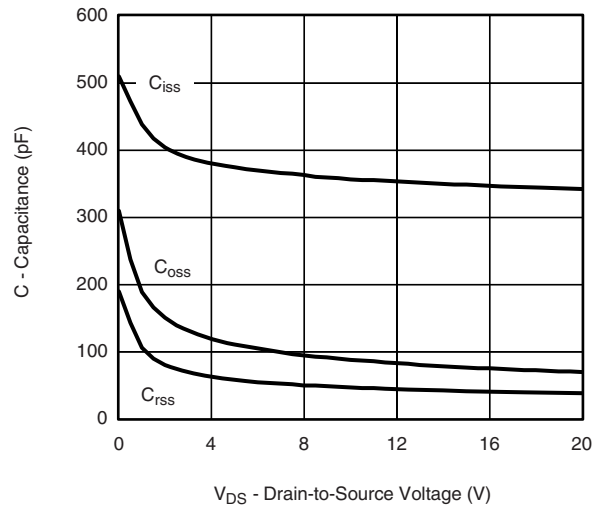
Output Characteristics



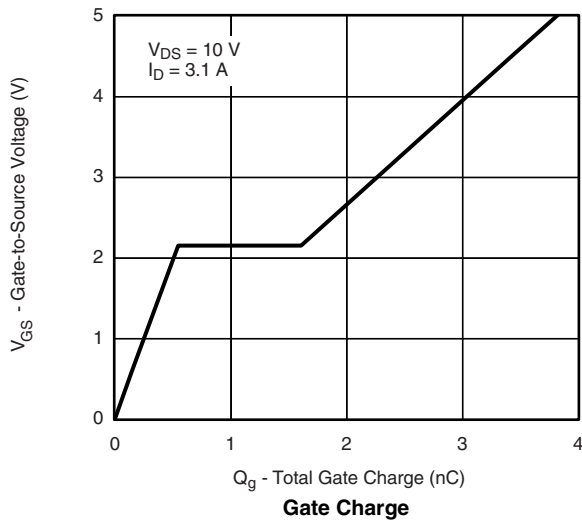
Transfer Characteristics



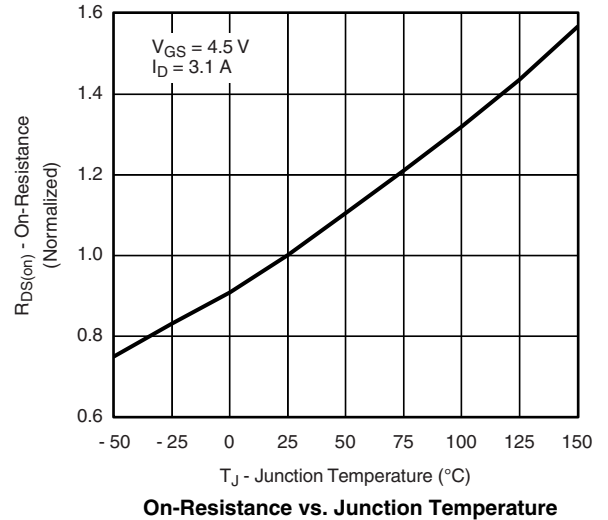
On-Resistance vs. Drain Current



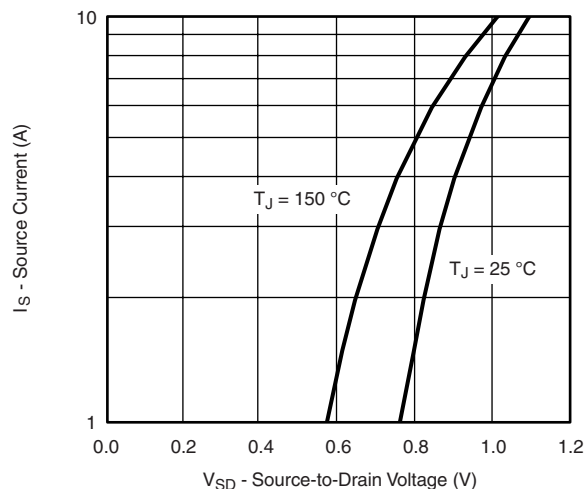
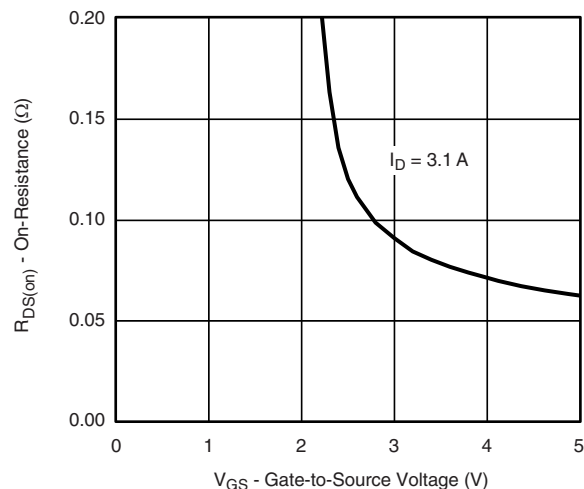
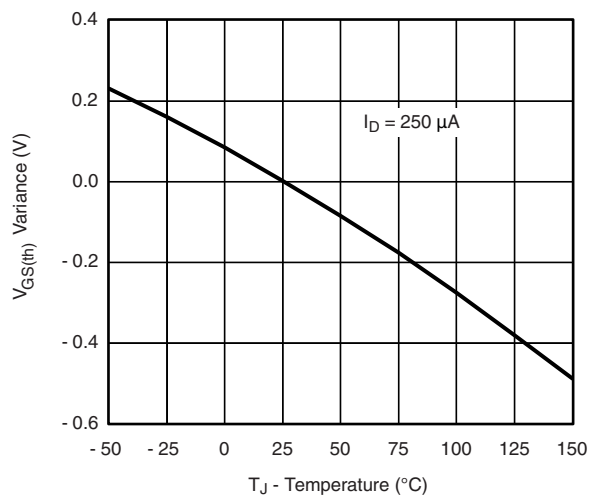
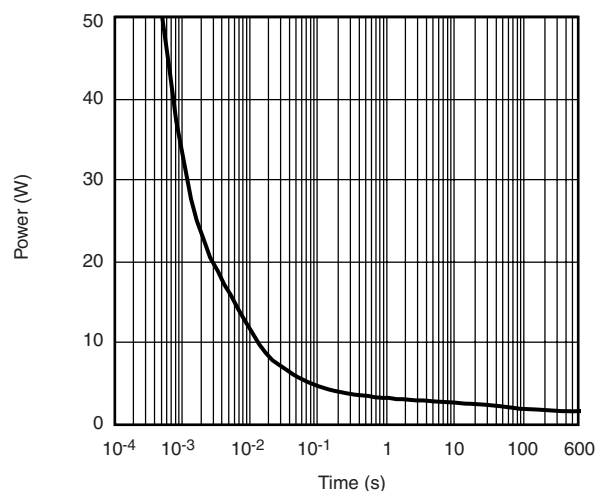
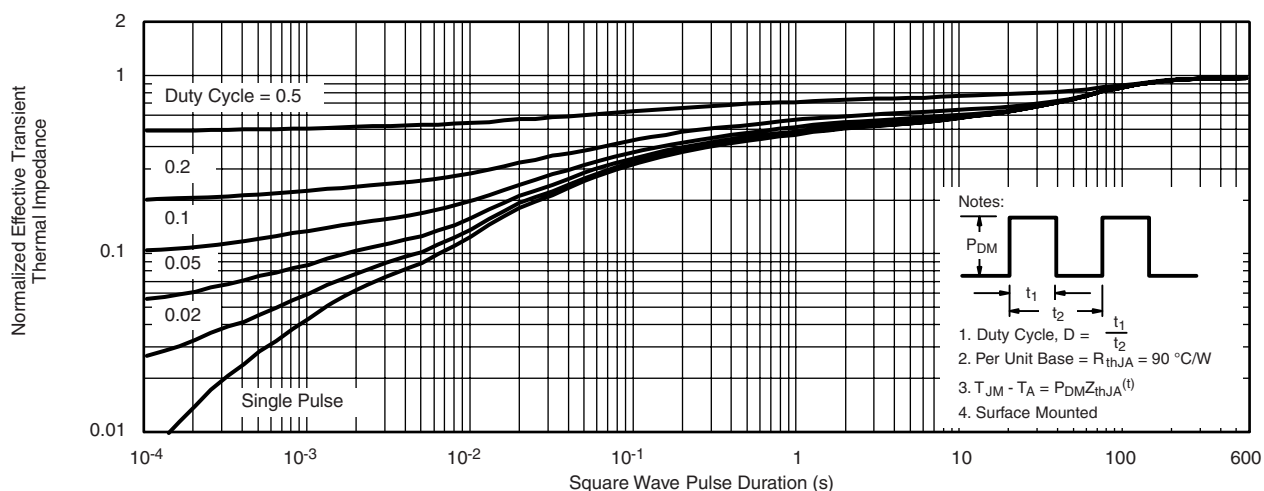
Capacitance



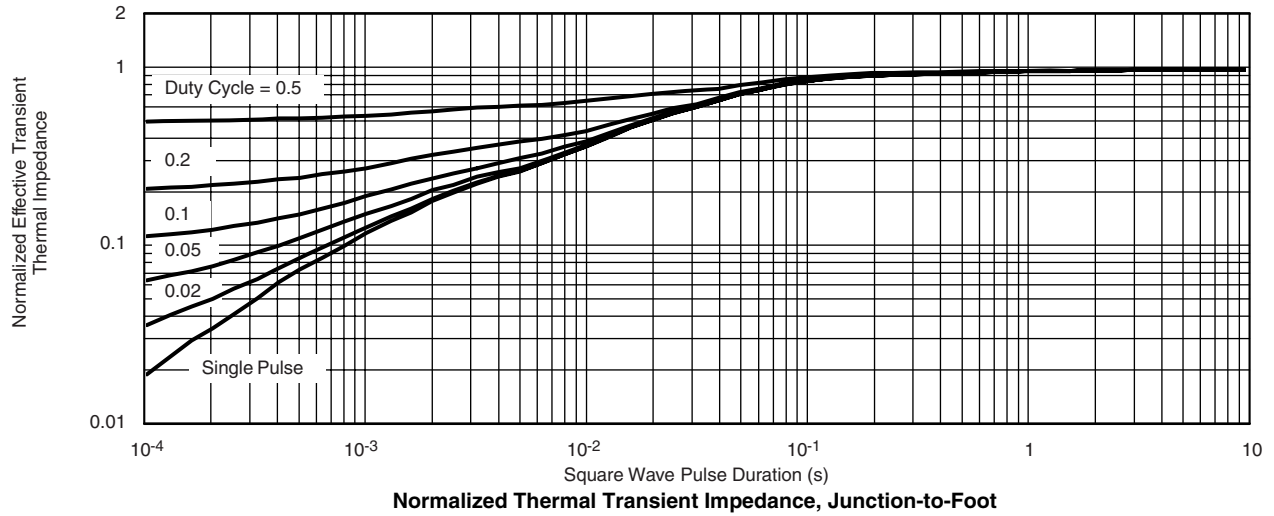
Gate Charge



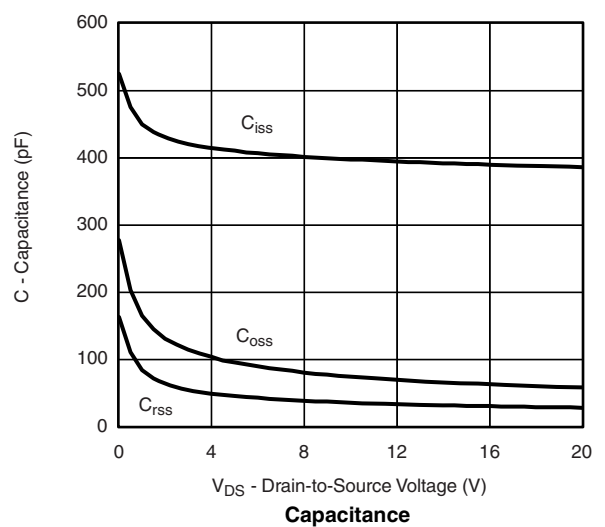
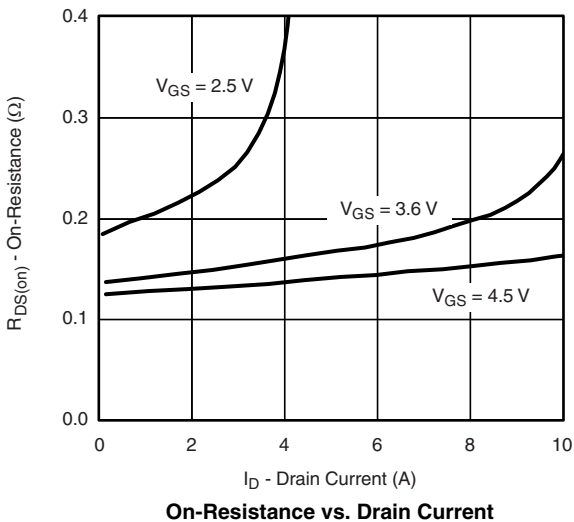
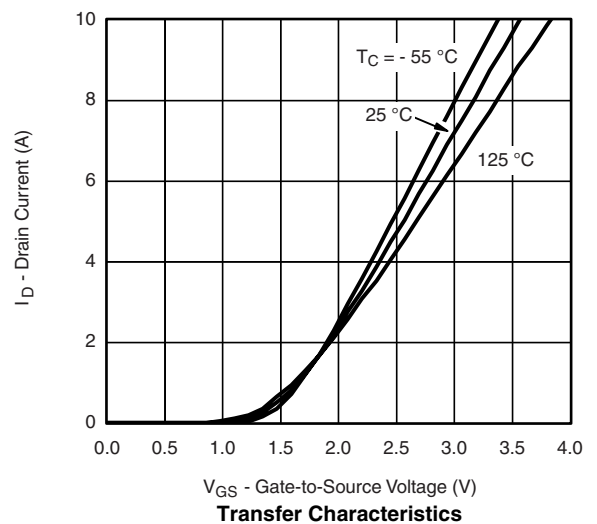
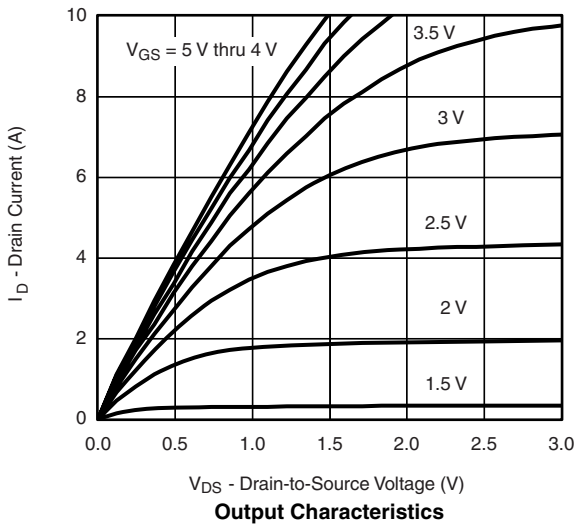
On-Resistance vs. Junction Temperature

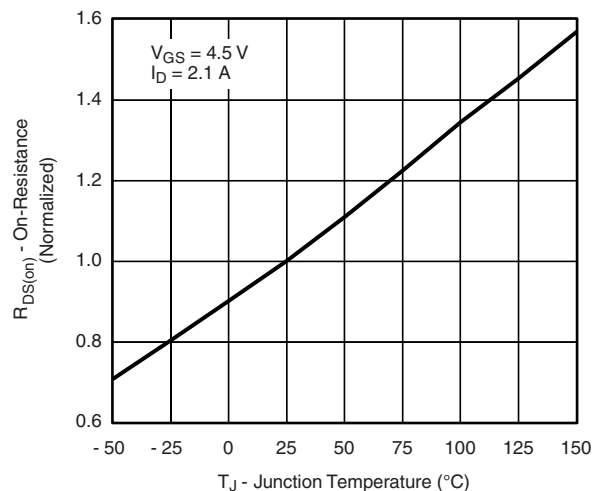
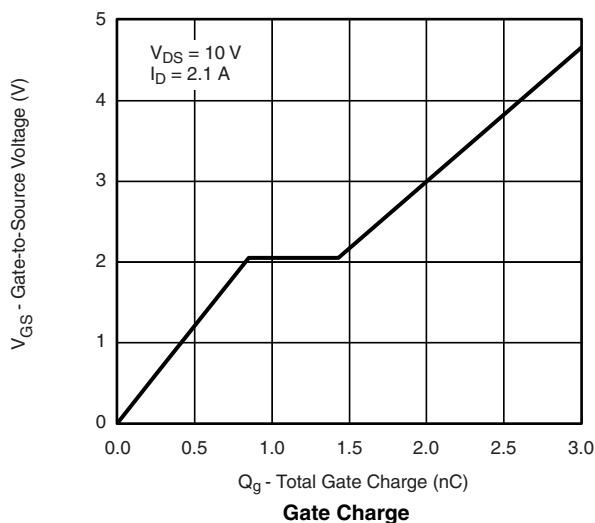
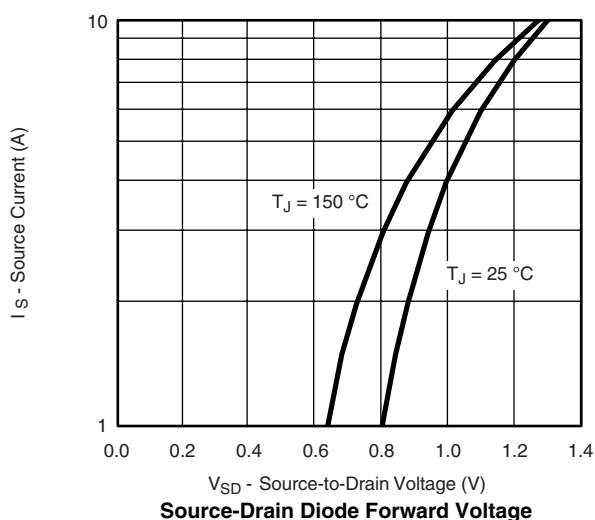
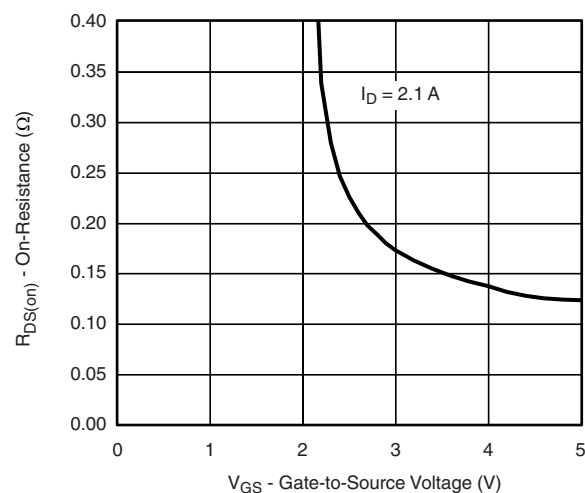
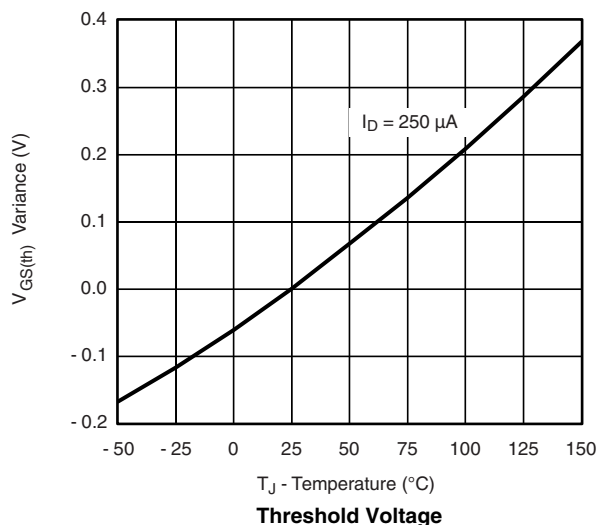
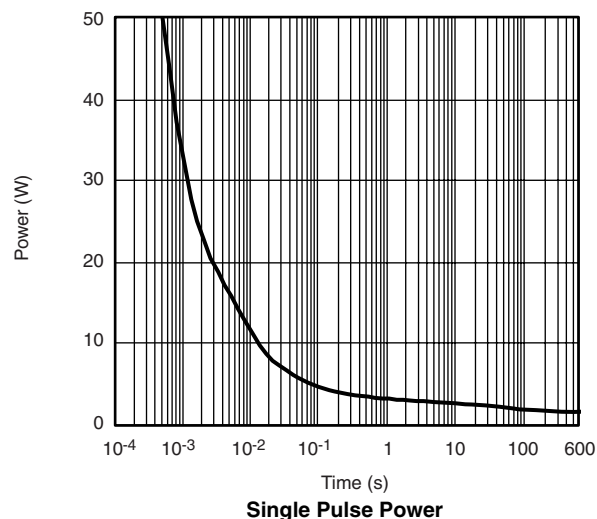
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power****Normalized Thermal Transient Impedance, Junction-to-Ambient**

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

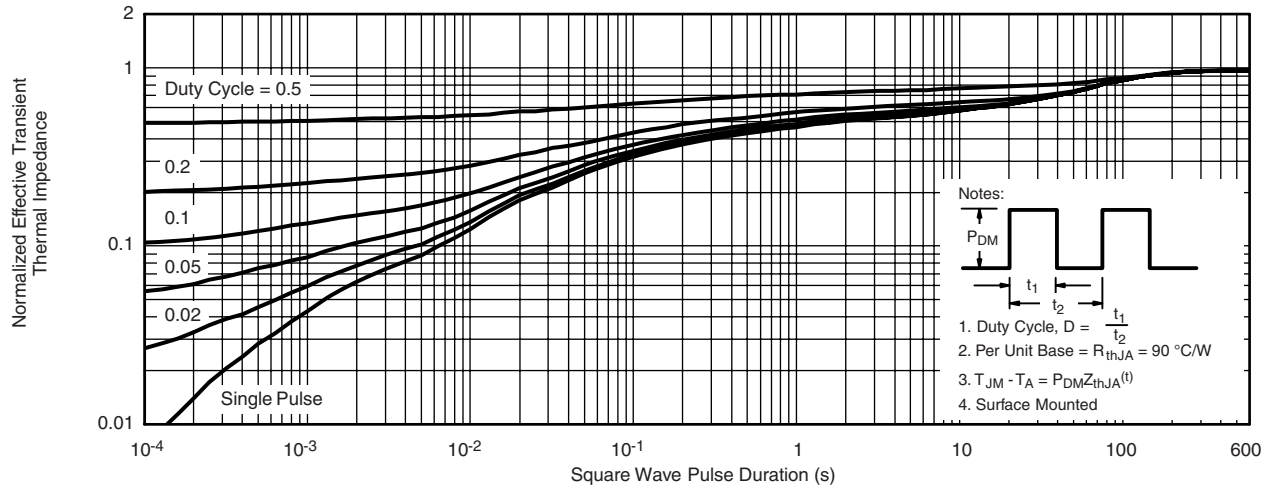


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

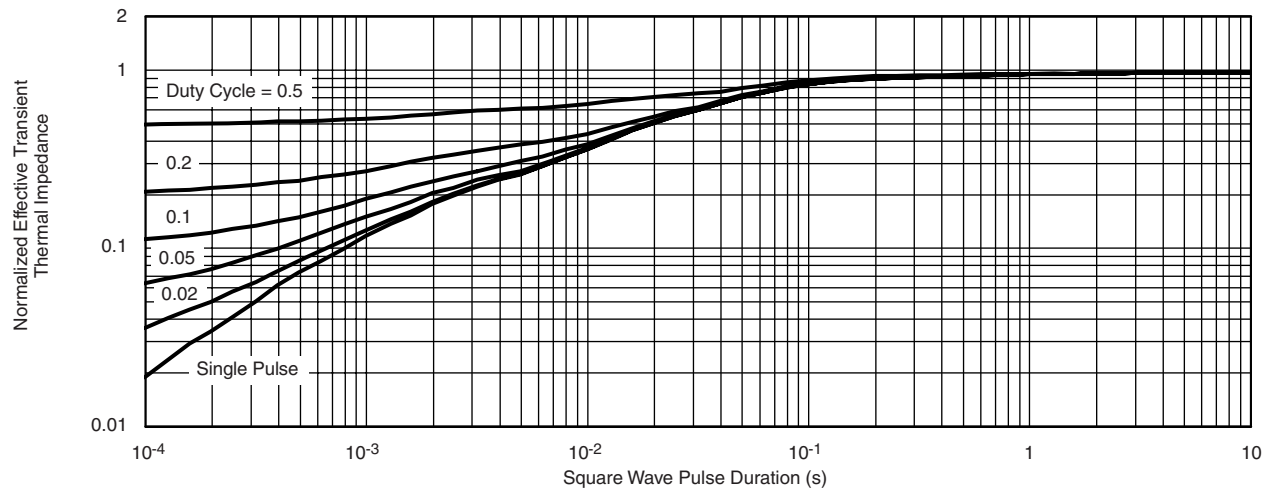


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power**

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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